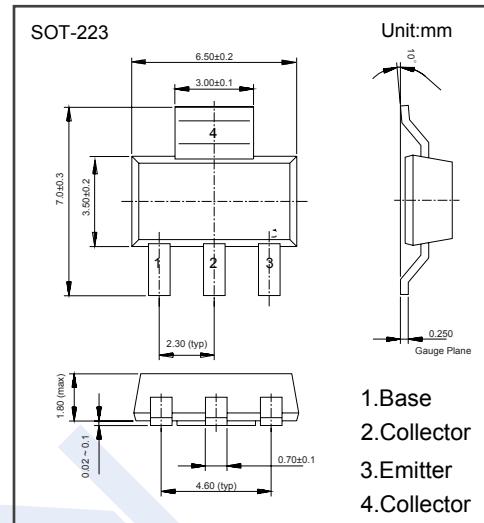


PNP Transistors**FZT953 (KZT953)****■ Features**

- Collector Current Capability $I_C = -5A$
- Collector Emitter Voltage $V_{CEO} = -100V$
- Complementary to FZT853

**■ Absolute Maximum Ratings $T_a = 25^\circ C$**

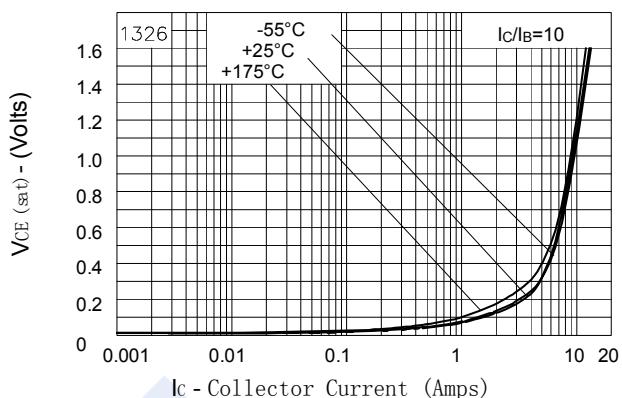
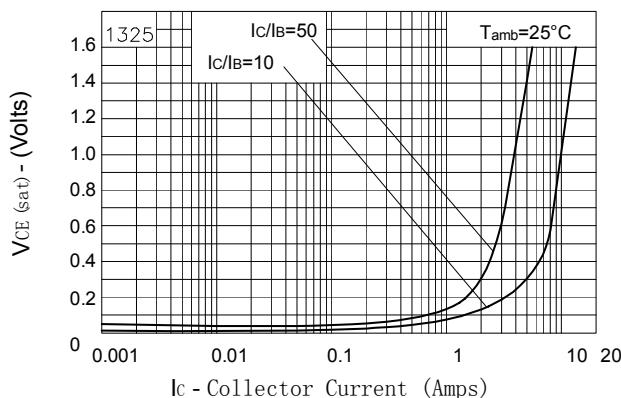
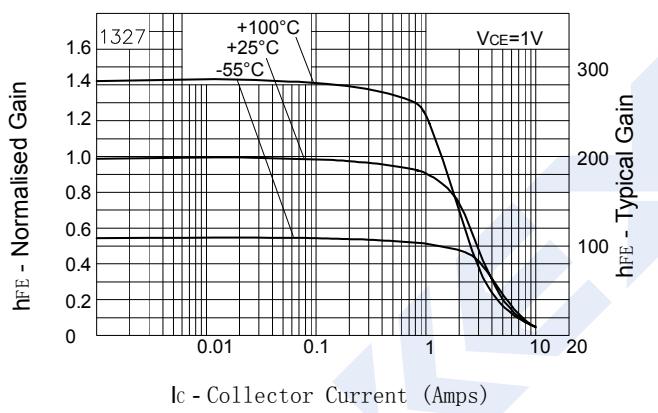
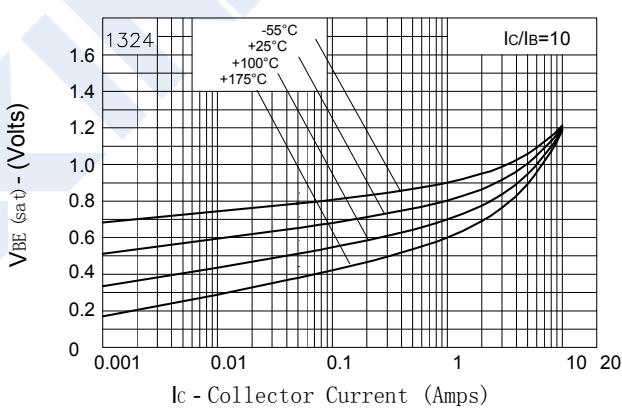
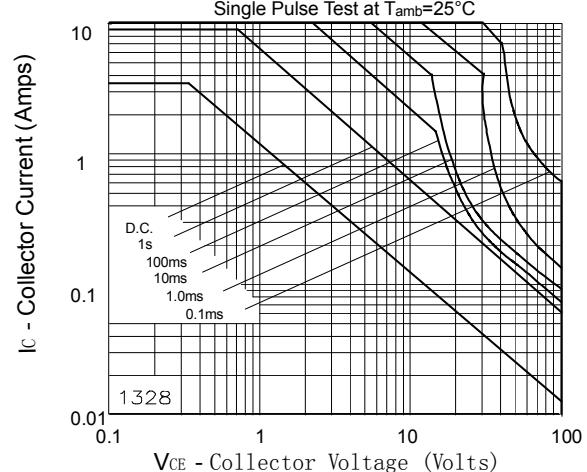
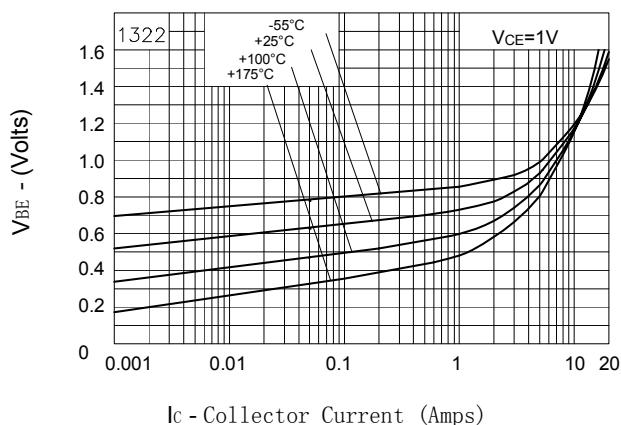
Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-140	V
Collector - Emitter Voltage	V_{CEO}	-100	
Emitter - Base Voltage	V_{EBO}	-6	
Collector Current - Continuous	I_C	-5	A
Collector Current - Pulse	I_{CP}	-10	
Collector Power Dissipation	P_C	3	W
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature range	T_{stg}	-55 to 150	

PNP Transistors**FZT953 (KZT953)**

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_c = -100 \mu A, I_E = 0$	-140			V
Collector-emitter breakdown voltage	V_{CER}	$I_c = -1 \mu A, R_B \leq 1 K\Omega$	-140			
	V_{CEO}	$I_c = -10 mA, I_B = 0$	-100			
Emitter-base breakdown voltage	V_{EBO}	$I_E = -100 \mu A, I_C = 0$	-6			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -100 V, I_E = 0$		-50	nA	nA
		$V_{CB} = -100 V, I_E = 0, T_a = 100^\circ C$		-1	uA	
Collector-emitter cut-off current ($R \leq 1 K\Omega$)	I_{CER}	$V_{CB} = -100 V, I_E = 0$		-50	nA	
		$V_{CB} = -100 V, I_E = 0, T_a = 100^\circ C$		-1	uA	
Emitter cut-off current	I_{EBO}	$V_{EB} = -6V, I_C = 0$		-10	nA	mV
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$ (Note.1)		-50		
		$I_C = -1 A, I_B = -100mA$ (Note.1)		-115		
		$I_C = -2 A, I_B = -200mA$ (Note.1)		-220		
		$I_C = -4 A, I_B = -400mA$ (Note.1)		-420		
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -4 A, I_B = -400mA$ (Note.1)		-1.17		V
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	$V_{CE} = -1V, I_C = -4A$ (Note.1)		-1.16		
DC current gain (Note.1)	$h_{FE}(1)$	$V_{CE} = -1V, I_C = -10mA$	100			
	$h_{FE}(2)$	$V_{CE} = -1V, I_C = -1A$	100		300	
	$h_{FE}(3)$	$V_{CE} = -1V, I_C = -3 A$	50			
	$h_{FE}(4)$	$V_{CE} = -1V, I_C = -4 A$	30			
	$h_{FE}(5)$	$V_{CE} = -1V, I_C = -10 A$		15		
Switching Times	t_{on}	$I_C = -2A, I_B1 = -200mA$ $I_B2 = 200mA, V_{CC} = -10V$		110		ns
	t_{off}			460		
Collector output capacitance	C_{ob}	$V_{CB} = -10V, f = 1MHz$ (Note.1)		65		pF
Transition frequency	f_T	$V_{CE} = -10V, I_C = -100mA, f = 50MHz$		125		MHz

Note.1: Pulse width=300 us. Duty cycle $\leq 2\%$

PNP Transistors**FZT953 (KZT953)****■ Typical Characteristics****V_{CE(sat)} v IC****V_{CE(sat)} v IC****hFE v IC****V_{BE(sat)} v IC****V_{BE(on)} v IC****Safe Operating Area**

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